

AMC3330-Q1 Precision, ± 1 -V Input, Reinforced Isolated Amplifier With Integrated DC/DC Converter

1 Features

- AEC-Q100 qualified for automotive applications:
 - Temperature grade 1: -40°C to 125°C , T_A
- 3.3-V or 5-V single supply with integrated DC/DC converter
- ± 1 -V input voltage range optimized for voltage measurements with high input impedance
- Fixed gain: 2.0
- Low DC errors:
 - Offset error: ± 0.5 mV (max)
 - Offset drift: ± 5 $\mu\text{V}/^{\circ}\text{C}$ (max)
 - Gain error: $\pm 0.4\%$ (max)
 - Gain drift: ± 60 ppm/ $^{\circ}\text{C}$ (max)
 - Initial nonlinearity: $\pm 0.075\%$ (max)
- High CMTI: 75 kV/ μs (min)
- System-level diagnostic features
- Safety-related certifications:
 - 6000- V_{PK} reinforced isolation per DIN VDE V 0884-11 (VDE V 0884-11): 2017-01
 - 4250- V_{RMS} isolation for 1 minute per UL1577
- Meets and exceeds CISPR-11 and CISPR-25 EMI standards

2 Applications

- Isolated voltage sensing in:
 - [HEV/EV onboard chargers \(OBC\)](#)
 - [HEV/EV DC/DC converters](#)
 - [HEV/EV traction inverters](#)

3 Description

The AMC3330-Q1 is a precision, isolated amplifier with a fully integrated, isolated DC/DC converter that allows single-supply operation from the low-side of the device. The reinforced capacitive isolation barrier is certified according to VDE V 0884-11 and UL1577 and separates sections of the system that operate on different common-mode voltage levels and protects low-voltage domains from damage.

The input of the AMC3330-Q1 is optimized for direct connection to high-impedance, voltage-signal sources such as a resistor-divider network to sense high-voltage signals. The integrated isolated DC/DC converter allows measurement of non-ground-referenced signals and makes the device a unique solution for space-constrained applications.

The excellent performance of the device supports accurate voltage monitoring and control. The integrated DC/DC converter fault-detection and diagnostic output pin of the AMC3330-Q1 simplify system-level design and diagnostics.

The AMC3330-Q1 is specified over the temperature range of -40°C to $+125^{\circ}\text{C}$.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
AMC3330-Q1	SOIC (16)	10.30 mm $\times$ 7.50 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Application Example

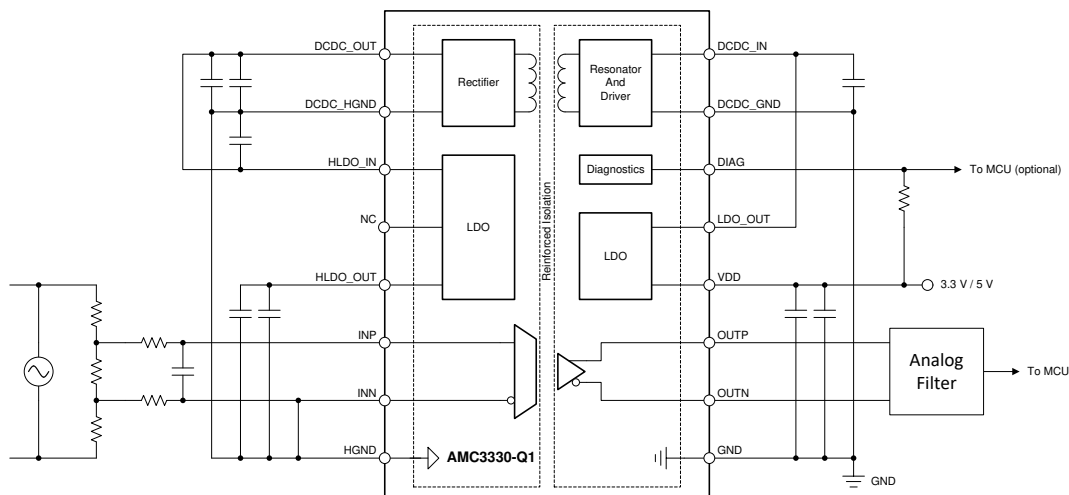


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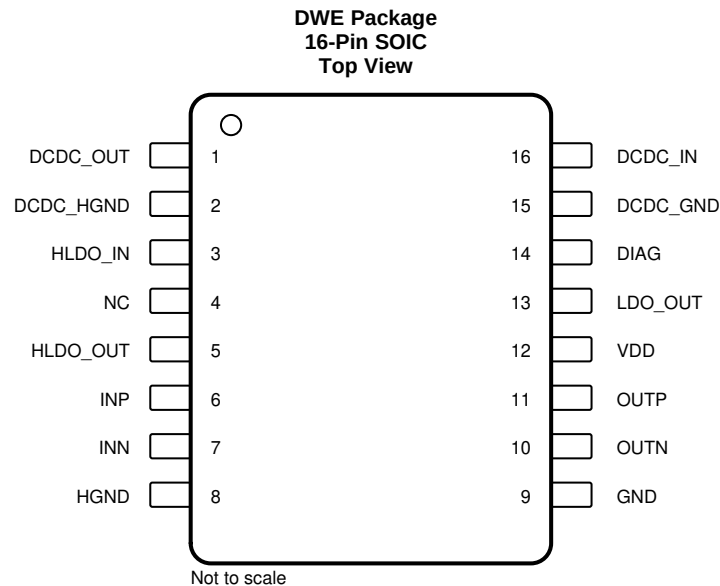
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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES
June 2020	*	Initial release.

5 Pin Configuration and Functions



Pin Functions

PIN		TYPE	DESCRIPTION
NO.	NAME		
1	DCDC_OUT	Power	High-side output of the isolated DC/DC converter; connect this pin to the HLDO_IN pin. See the Power Supply Recommendations section for power-supply decoupling recommendations.
2	DCDC_HGND	Power	High-side ground reference for the isolated DC/DC converter; connect this pin to the HGND pin.
3	HLDO_IN	Power	Input of the high-side low-dropout (LDO) regulator; connect this pin to the DCDC_OUT pin. See the Power Supply Recommendations section for power-supply decoupling recommendations.
4	NC	—	No internal connection. Connect this pin to the high-side ground or leave this pin unconnected (floating).
5	HLDO_OUT	Power	Output of the high-side LDO. See the Power Supply Recommendations section for power-supply decoupling recommendations.
6	INP	Input	Noninverting analog input.
7	INN	Input	Inverting analog input. Connect this pin to HGND.
8	HGND	Analog	High-side analog ground; connect this pin to the DCDC_HGND pin.
9	GND	Analog	Low-side analog ground; connect this pin to the DCDC_GND pin.
10	OUTN	Output	Inverting analog output.
11	OUTP	Output	Noninverting analog output.
12	VDD	Power	Low-side power supply. See the Power Supply Recommendations section for power-supply decoupling recommendations.
13	LDO_OUT	Power	Output of the primary-side LDO; connect this pin to the DCDC_IN pin. See the Power Supply Recommendations section for power-supply decoupling recommendations.
14	DIAG	Output	Active-low, open-drain status indicator output; connect this pin to the pullup supply (for example, VDD) using a resistor or leave this pin floating if not used.
15	DCDC_GND	Power	Low-side ground reference for the isolated DC/DC converter; connect this pin to the GND pin.
16	DCDC_IN	Power	Primary-side input of the isolated DC/DC converter; connect this pin to the LDO_OUT pin. See the Power Supply Recommendations section for power-supply decoupling recommendations.

6 Specifications

6.1 Absolute Maximum Ratings

see ⁽¹⁾

		MIN	MAX	UNIT
Power-supply voltage	VDD to GND	–0.3	6.5	V
Analog input voltage	INP, INN	HGND – 6	HLDO_OUT + 0.5	V
Analog output voltage	OUTP, OUTN	GND – 0.5	VDD + 0.5	V
Digital output voltage	DIAG	GND – 0.5	5.5	V
Input current	Continuous, any pin except power-supply pins	–10	10	mA
Temperature	Junction, T _J		150	°C
	Storage, T _{stg}	–65	150	

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 ⁽¹⁾ , HBM ESD classification Level 2	±2000	V
		Charged-device model (CDM), per AEC Q100-011, CDM ESD classification Level C6	±1000	

- (1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification

6.3 Recommended Operating Conditions

over operating ambient temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
POWER SUPPLY						
VDD	Low-side supply voltage	VDD to GND	3.0	3.3	5.5	V
ANALOG INPUT						
V _{Clipping}	Differential input voltage before clipping output	V _{IN} = V _{INP} – V _{INN}	±1.25			V
V _{FSR}	Specified linear differential full-scale voltage	V _{IN} = V _{INP} – V _{INN}	–1		1	V
	Absolute common-mode input voltage ⁽¹⁾	(V _{INP} + V _{INN}) / 2 to HGND	–2		3	V
V _{CM}	Operating common-mode input voltage	(V _{INP} + V _{INN}) / 2 to HGND, V _{INP} = V _{INN}	–1.4		1.6	V
		(V _{INP} + V _{INN}) / 2 to HGND, V _{INP} – V _{INN} = 1.25 V	–0.8		0.6	
TEMPERATURE RANGE						
T _A	Operating ambient temperature		–40	25	125	°C

- (1) Steady-state voltage supported by the device in case of a system failure. See specified common-mode input voltage V_{CM} for normal operation. Observe analog input voltage range as specified in the *Absolute Maximum Ratings* table.

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		AMC3330-Q1	UNIT
		DWL (SOIC)	
		16 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	73.5	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	31	°C/W
R _{θJB}	Junction-to-board thermal resistance	44	°C/W
Y _{JT}	Junction-to-top characterization parameter	16.7	°C/W
Y _{JB}	Junction-to-board characterization parameter	42.8	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	n/a	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Power Ratings

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
P _D	Maximum power dissipation	VDD = 5.5 V			170.5	mW
		VDD = 3.6 V			108	

6.6 Insulation Specifications

over operating ambient temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	VALUE	UNIT
GENERAL				
CLR	External clearance ⁽¹⁾	Shortest pin-to-pin distance through air	≥ 8	mm
CPG	External creepage ⁽¹⁾	Shortest pin-to-pin distance across the package surface	≥ 8	mm
DTI	Distance through the insulation	Minimum internal gap (internal clearance - capacitive signal isolation)	≥ 21	μm
		Minimum internal gap (internal clearance - transformer power isolation)	≥ 120	
CTI	Comparative tracking index	DIN EN 60112 (VDE 0303-11); IEC 60112	≥ 600	V
	Material group	According to IEC 60664-1	I	
	Overvoltage category per IEC 60664-1	Rated mains voltage ≤ 600 V _{RMS}	I-IV	
		Rated mains voltage ≤ 1000 V _{RMS}	I-III	
DIN VDE V 0884-11 (VDE V 0884-11): 2017-01				
V _{IORM}	Maximum repetitive peak isolation voltage	At AC voltage (bipolar)	1700	V _{PK}
V _{IOWM}	Maximum-rated isolation working voltage	At AC voltage (sine wave); time-dependent dielectric breakdown (TDDB) test	1200	V _{RMS}
		At DC voltage	1700	V _{DC}
V _{IOTM}	Maximum transient isolation voltage	V _{TEST} = V _{IOTM} , t = 60 s (qualification test)	6000	V _{PK}
		V _{TEST} = 1.2 × V _{IOTM} , t = 1 s (100% production test)	7200	V _{PK}
V _{IOSM}	Maximum surge isolation voltage ⁽²⁾	Test method per IEC 60065, 1.2/50-μs waveform, V _{TEST} = 1.6 × V _{IOSM} = 10000 V _{PK} (qualification)	6250	V _{PK}
q _{pd}	Apparent charge ⁽³⁾	Method a, after input/output safety test subgroup 2 / 3, V _{ini} = V _{IOTM} , t _{ini} = 60 s, V _{pd(m)} = 1.2 × V _{IORM} , t _m = 10 s	≤ 5	pC
		Method a, after environmental tests subgroup 1, V _{ini} = V _{IOTM} , t _{ini} = 60 s, V _{pd(m)} = 1.6 × V _{IORM} , t _m = 10 s	≤ 5	
		Method b1, at routine test (100% production) and preconditioning (type test), V _{ini} = V _{IOTM} , t _{ini} = 1 s, V _{pd(m)} = 1.875 × V _{IORM} , t _m = 1 s	≤ 5	
C _{IO}	Barrier capacitance, input to output ⁽⁴⁾	V _{IO} = 0.5 V _{PP} at 1 MHz	~3.5	pF
R _{IO}	Insulation resistance, input to output ⁽⁴⁾	V _{IO} = 500 V at T _A = 25°C	> 10 ¹²	Ω
		V _{IO} = 500 V at 100°C ≤ T _A ≤ 125°C	> 10 ¹¹	
		V _{IO} = 500 V at T _S = 150°C	> 10 ⁹	
	Pollution degree		2	
	Climatic category		40/125/21	
UL1577				
V _{ISO}	Withstand isolation voltage	V _{TEST} = V _{ISO} = 5000 V _{RMS} or 7071 V _{DC} , t = 60 s (qualification), V _{TEST} = 1.2 × V _{ISO} , t = 1 s (100% production test)	4250	V _{RMS}

- (1) Apply creepage and clearance requirements according to the specific equipment isolation standards of an application. Care must be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed circuit board (PCB) do not reduce this distance. Creepage and clearance on a PCB become equal in certain cases. Techniques such as inserting grooves, ribs, or both on a PCB are used to help increase these specifications.
- (2) Testing is carried out in air or oil to determine the intrinsic surge immunity of the isolation barrier.
- (3) Apparent charge is electrical discharge caused by a partial discharge (pd).
- (4) All pins on each side of the barrier are tied together, creating a two-pin device.

6.7 Safety-Related Certifications

VDE	UL
Certified according to DIN VDE V 0884-11 (VDE V 0884-11): 2017-01, DIN EN 60950-1 (VDE 0805 Teil 1): 2014-08, and DIN EN 60065 (VDE 0860): 2005-11	Recognized under 1577 component recognition and CSA component acceptance NO 5 programs
Reinforced insulation	Single protection
Certificate planned	Certificate planned

6.8 Safety Limiting Values

Safety limiting ⁽¹⁾ intends to minimize potential damage to the isolation barrier upon failure of input or output circuitry. A failure of the I/O can allow low resistance to ground or the supply and, without current limiting, dissipate sufficient power to over-heat the die and damage the isolation barrier potentially leading to secondary system failures.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _S	R _{θJA} = 73.5°C/W, VDD = 5.5 V, T _J = 150°C, T _A = 25°C			309	mA
	R _{θJA} = 73.5°C/W, VDD = 3.6 V, T _J = 150°C, T _A = 25°C			472	
P _S	R _{θJA} = 73.5°C/W, T _J = 150°C, T _A = 25°C			1700	mW
T _S				150	°C

- (1) The maximum safety temperature, T_S, has the same value as the maximum junction temperature, T_J, specified for the device. The I_S and P_S parameters represent the safety current and safety power, respectively. Do not exceed the maximum limits of I_S and P_S. These limits vary with the ambient temperature, T_A.

The junction-to-air thermal resistance, R_{θJA}, in the [Thermal Information](#) table is that of a device installed on a high-K test board for leaded surface-mount packages. Use these equations to calculate the value for each parameter:

T_J = T_A + R_{θJA} × P, where P is the power dissipated in the device.

T_{J(max)} = T_S = T_A + R_{θJA} × P_S, where T_{J(max)} is the maximum junction temperature.

P_S = I_S × VDD_{max}, where VDD_{max} is the maximum low-side voltage.

6.9 Electrical Characteristics

minimum and maximum specifications apply from T_A = –40°C to +125°C, VDD = 3.0 V to 5.5 V, INP = –1V to +1 V, and INN = HGND = 0V; typical specifications are at T_A = 25°C, and VDD = 3.3 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ANALOG INPUT						
R _{IN}	Single-ended input resistance	INN = HGND	0.1	1.5		GΩ
R _{IND}	Differential input resistance		0.16	1.5		
I _{IB}	Input bias current	INP = INN = HGND, I _{IB} = (I _{IBP} + I _{IBN}) / 2	–10		10	nA
TC _{I_{IB}}	Input bias current drift			–14		pA/°C
I _{IO}	Input offset current	I _{IO} = I _{INP} – I _{INN}	–5		5	nA
C _{IN}	Single-ended input capacitance	INN = HGND, f _{IN} = 310 kHz		2		pF
C _{IND}	Differential input capacitance	f _{IN} = 310 kHz		2		

Electrical Characteristics (continued)

minimum and maximum specifications apply from $T_A = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$, $V_{DD} = 3.0\text{ V}$ to 5.5 V , $\text{INP} = -1\text{ V}$ to $+1\text{ V}$, and $\text{INN} = \text{HGND} = 0\text{ V}$; typical specifications are at $T_A = 25^{\circ}\text{C}$, and $V_{DD} = 3.3\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ANALOG OUTPUT						
	Nominal gain		2			
V _{CMout}	Common-mode output voltage		1.39	1.44	1.49	V
BW _{OUT}	Output bandwidth		250	310		kHz
R _{OUT}	Output resistance	On OUTP or OUTN	0.2			Ω
	Output short-circuit current	On OUTP or OUTN	−14			mA
CMTI	Common-mode transient immunity	HGND – GND = 2 kV	75	130		kV/μs
ACCURACY						
E _G	Gain error ⁽¹⁾	Initial, at T _A = 25°C	−0.4			0.4 %
TCE _G	Gain error drift ⁽¹⁾		−60			60 ppm/°C
V _{OS}	Input offset voltage ⁽¹⁾	Initial, at T _A = 25°C, INP = INN = HGND ⁽²⁾	−0.5			0.5 mV
TCV _{OS}	Input offset drift ⁽¹⁾		−5			5 μV/°C
	Nonlinearity ⁽¹⁾		−0.075			0.075 %
	Nonlinearity drift		−1			1 ppm/°C
SNR	Signal-to-noise ratio	V _{IN} = 1 V _{PP} , f _{IN} = 1 kHz, BW = 10 kHz	80	85	dB	
		V _{IN} = 1 V _{PP} , f _{IN} = 100 kHz, BW = 100 kHz	72			
THD	Total harmonic distortion	V _{IN} = 0.5 V _{pp} , f _{IN} = 10 kHz, BW = 100 kHz	−85			dB
	Output noise	INP = INN = HGND, f _{IN} = 0 Hz, BW = 100 kHz	220			μV _{RMS}
CMRR	Common-mode rejection ratio	f _{IN} = 0 Hz, V _{CM min} ≤ V _{CM} ≤ V _{CM max}	−100			dB
		f _{IN} = 10 kHz, V _{CM min} ≤ V _{CM} ≤ V _{CM max}	−98			
PSRR	Power-supply rejection ratio	VDD at dc	−103			dB
		100-mV, 10-kHz ripple on VDD	−86			
POWER SUPPLY						
IDD	Low-side supply current	4.5 V ≤ VDD ≤ 5.5 V	28.5			31 mA
		3.0 V ≤ VDD ≤ 3.6 V	27.5			30 mA
V _{DCDC_O UT}	DC/DC output voltage	DCDCout to HGND	3.3	3.6	4.2	V
V _{HLDO_O UT}	High-side LDO output voltage	HLDO to HGND, no external load	3	3.2	3.4	V
		HLDO to HGND, 1 mA external load on HLDO	3	3.2	3.4	
I _H	High-side supply current for auxiliary circuitry	Load connected from HLDO_OUT to HGND; non-switching				1 mA

(1) The typical value includes one sigma statistical variation.

(2) The typical value is at $V_{\text{DD}} = 3.3\text{ V}$.

6.10 Switching Characteristics

over operating ambient temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_r	Output signal rise time		1.3		μs
t_f	Output signal fall time		1.3		μs
	V_{INX} to V_{OUTX} signal delay (50% – 10%)		1	1.5	μs
	V_{INX} to V_{OUTX} signal delay (50% – 50%)		1.6	2.1	μs
	V_{INX} to V_{OUTX} signal delay (50% – 90%)		2.5	3	μs
t_{AS}	Analog settling time			1.5	ms
	VDD step to 3.0 V, to OUTP and OUTN valid, 0.1% settling				

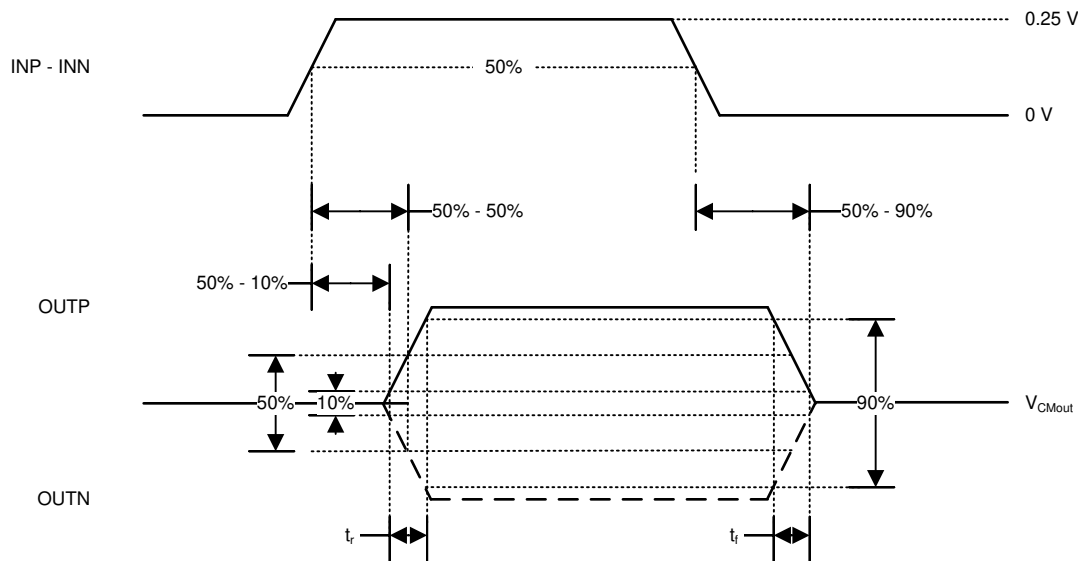


Figure 1. Rise, Fall, and Delay Time Waveforms

6.11 Insulation Characteristics Curves

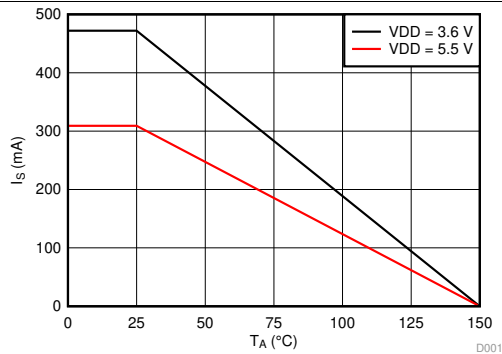


Figure 2. Thermal Derating Curve for Safety-Limiting Current per VDE

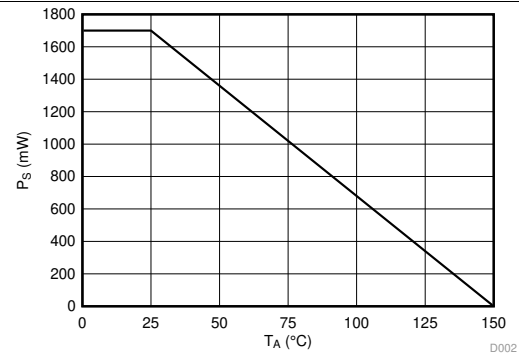
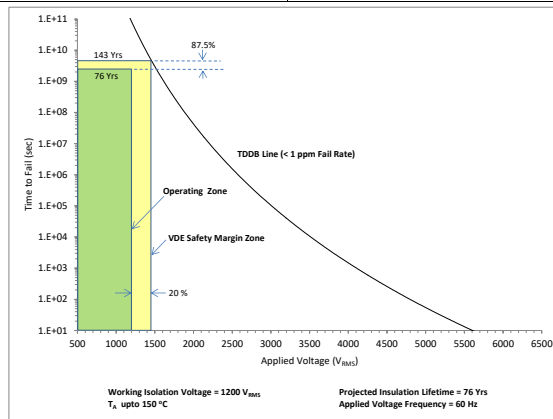


Figure 3. Thermal Derating Curve for Safety-Limiting Power per VDE



TA up to 150°C, stress-voltage frequency = 60 Hz,
isolation working voltage = 1200 VRMS, operating lifetime = 76 years

Figure 4. Reinforced Isolation Capacitor Lifetime Projection

7 Detailed Description

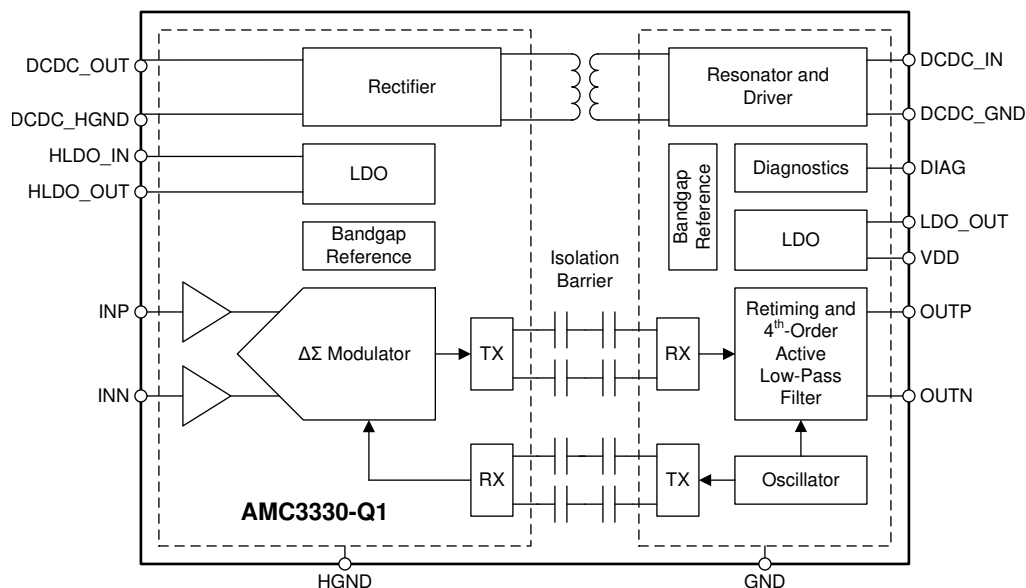
7.1 Overview

The AMC3330-Q1 is a fully-differential, precision, isolated amplifier with high input impedance, and an integrated DC/DC converter that allows the device to be supplied from a single 3.3-V or 5-V voltage supply source on the low side. The input stage of the device drives a second-order, delta-sigma ($\Delta\Sigma$) modulator. The modulator uses the internal voltage reference and clock generator to convert the analog input signal to a digital bitstream. The drivers (termed TX in the [Functional Block Diagram](#)) transfer the output of the modulator across the isolation barrier that separates the high-side and low-side voltage domains. The received bitstream and clock are synchronized and processed by a fourth-order analog filter on the low-side and presented as a differential analog output.

The [Functional Block Diagram](#) shows a detailed block diagram of the AMC3330-Q1. The 1.6-G Ω differential input impedance of the analog input stage supports low gain-error signal-sensing in high-voltage applications using resistive dividers.

The silicon-dioxide (SiO₂)-based capacitive isolation barrier supports a high level of magnetic field immunity, as described in the [ISO72x Digital Isolator Magnetic-Field Immunity application report](#), available for download at www.ti.com.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Analog Input

The input stage of the AMC3330-Q1 feeds a second-order, switched-capacitor, feed-forward $\Delta\Sigma$ modulator. The modulator converts the analog signal into a bitstream that is transferred over the isolation barrier, as described in the [Isolation Channel Signal Transmission](#) section. The high-impedance, and low bias-current input of the AMC3330-Q1 makes the device suitable for isolated, high-voltage-sensing applications that typically employ high-impedance resistor dividers.

There are two restrictions on the analog input signals (INP and INN). First, if the input voltage exceeds the range $\text{HGND} - 6 \text{ V}$ to $\text{V}_{\text{HLDO\_OUT}} + 0.5 \text{ V}$, the input current must be limited to 10 mA because the device input electrostatic discharge (ESD) diodes turn on. In addition, the linearity and noise performance of the device are ensured only when the differential analog input voltage remains within the specified linear full-scale range (FSR) of $\pm 1 \text{ V}$, and within the specified input common-mode voltage range.

Feature Description (continued)

7.3.2 Isolation Channel Signal Transmission

The AMC3330-Q1 uses an on-off keying (OOK) modulation scheme to transmit the modulator output-bitstream across the capacitive SiO₂-based isolation barrier. Figure 5 shows the block diagram of an isolation channel. The transmitter modulates the bitstream at TX IN with an internally generated, 480-MHz carrier and sends a burst across the isolation barrier to represent a digital *one* and sends a *no signal* to represent the digital *zero*. The receiver demodulates the signal after advanced signal conditioning and produces the output. The symmetrical design of each isolation channel improves the common-mode transient immunity (CMTI) performance and reduces the radiated emissions caused by the high-frequency carrier.

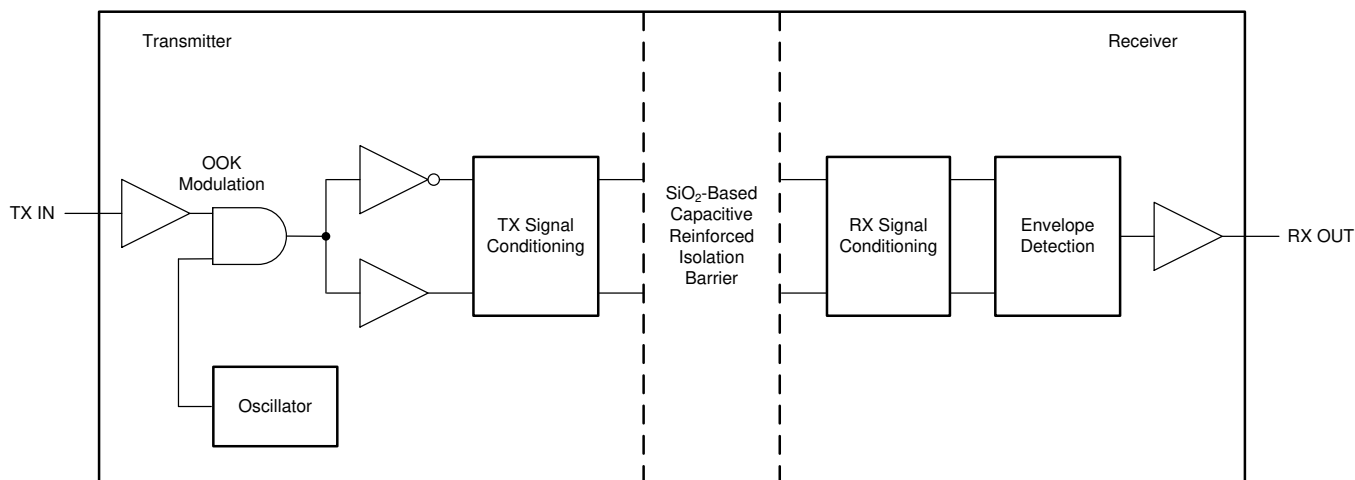


Figure 5. Block Diagram of an Isolation Channel

Figure 6 shows the concept of the on-off keying scheme.

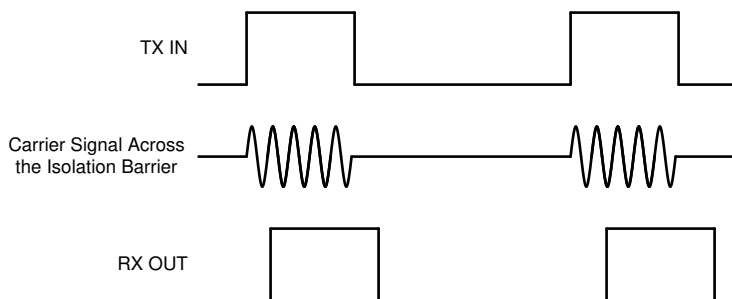


Figure 6. OOK-Based Modulation Scheme

Feature Description (continued)

7.3.3 Isolated DC/DC Converter

The AMC3330-Q1 offers a fully integrated isolated DC/DC converter stage that includes the following components illustrated in the [Functional Block Diagram](#):

- Low-dropout regulator (LDO) on the primary side to stabilize the supply voltage VDD that drives the primary side of the converter
- Primary full-bridge inverter and drivers
- Laminate-based, air-core transformer for high immunity to magnetic fields
- Secondary full-bridge rectifier
- Secondary LDO to stabilize the output voltage of the DC/DC converter for high analog performance of the signal path

The DC/DC converter uses a spread-spectrum clock generation technique to reduce the spectral density of the electromagnetic radiation. The resonator frequency is synchronous to the operation of the $\Delta\Sigma$ modulator to minimize interference with data transmission and support the high analog performance of the device.

The architecture of the DC/DC converter is optimized to drive the high-side circuitry of the AMC3330-Q1 and can source up to 1 mA of additional current (I_H) for an optional external circuit (such as an active filter, pre-amplifier, or comparator).

7.3.4 Analog Output

The AMC3330-Q1 offers a differential analog output comprised of the OUTP and OUTN pins. For differential input voltages ($V_{INP} - V_{INN}$) in the range from -1 V to 1 V , the device provides a linear response with a nominal gain of 2. For example, for a differential input voltage of 1 V , the differential output voltage ($V_{OUTP} - V_{OUTN}$) is 2 V . At zero input (INP shorted to INN), both pins output the same common-mode output voltage V_{CMout} , as specified in the *Electrical Characteristics* table in the [Specifications](#) section. For absolute differential input voltages greater than 1.0 V but less than 1.25 V , the differential output voltage continues to increase in magnitude but with reduced linearity performance. The outputs saturate as shown in [Figure 7](#) if the differential input voltage exceeds the $V_{Clipping}$ value.

The AMC3330-Q1 provides a fail-safe output behavior in case the high-side supply fails. See the [Diagnostic Output and Fail-Safe Behavior](#) section for more details.

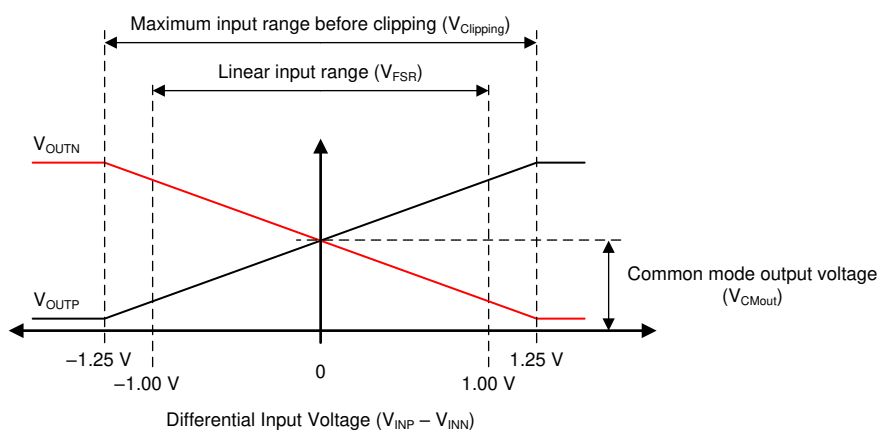


Figure 7. AMC3330-Q1 Output Behavior

Feature Description (continued)

7.3.5 Diagnostic Output and Fail-Safe Behavior

The open-drain DIAG pin can be monitored to confirm the device is operational, and the output voltage is valid. During power-up, the DIAG pin is actively held low until the high-side supply is in regulation and the device operates properly. The DIAG pin is actively pulled low if:

- The low-side does not receive data from the high-side (for example, because of a loss of power on the high-side). The amplifier outputs are driven to negative full-scale.
- The high-side DC/DC output voltage (DCDC_OUT) or the high-side LDO output voltage (HLDO_OUT) drop below their respective undervoltage detection thresholds (brown-out). In this case, the low-side may still receive data from the high-side but the data may not be valid. The amplifier outputs are driven to negative full-scale.

During normal operation, the DIAG pin is in a high-impedance state. Connect the DIAG pin to a pullup supply through a resistor or leave open if not used.

7.4 Device Functional Modes

The AMC3330-Q1 is operational when the power supply VDD is applied, as specified in the *Recommended Operating Conditions* table in the [Specifications](#) section.

8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The low input bias current, AC and DC errors, and temperature drift make the AMC3330-Q1 a high-performance solution for applications where voltage measurement with high common-mode levels is required.

8.2 Typical Application

Isolated amplifiers are widely used for voltage measurements in high-voltage applications that must be isolated from a low-voltage domain. Typical applications are AC line voltage measurements at the input of a power factor correction (PFC) stage of an onboard charger (OBC). Other applications are DC measurements at the output of a PFC stage or DC/DC converter, or phase voltage measurements in traction inverters. The AMC3330-Q1 integrates an isolated power supply for the high-voltage side and therefore is particularly easy to use in applications that do not have a high-side supply readily available or where a high-side supply is referenced to a different ground potential than the signal to be measured.

Figure 8 illustrates a simplified schematic of the AMC3330-Q1 in an OBC where the AC phase voltage on the grid-side must to be measured. At that location in the system, there is no supply readily available for powering the isolated amplifier. The integrated isolated power supply, together with its bipolar input voltage range, makes the AMC3330-Q1 ideally suited for AC line-voltage sensing. In this example, the output current of the PFC is sensed by the [AMC3301](#) across a shunt resistor on the positive DC-link rail where there is also no suitable supply available for powering the isolated amplifier. The integrated power-supply of the AMC3301 eliminates that problem and enables current sensing at optimal locations for the system.

Typical Application (continued)

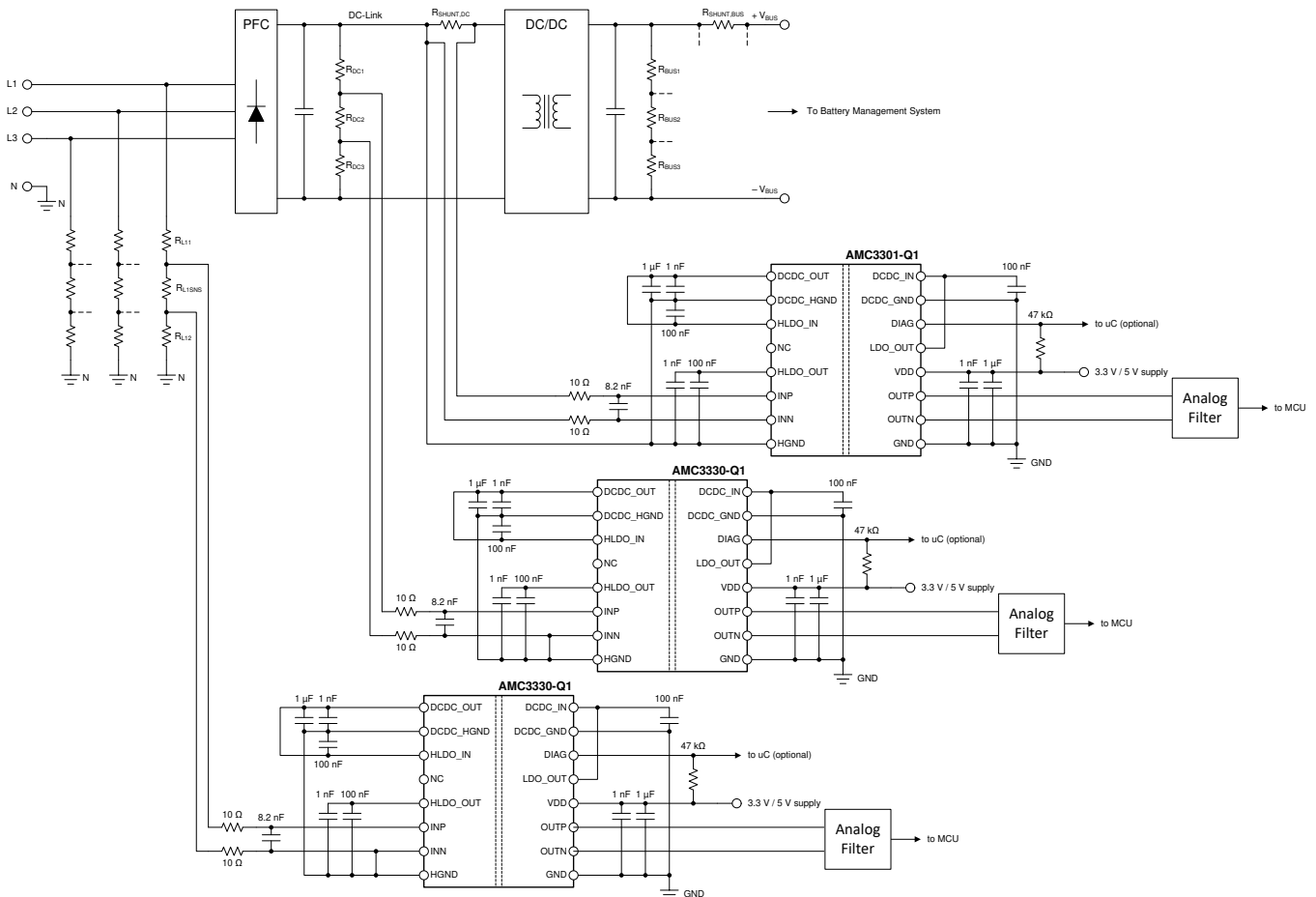


Figure 8. The AMC3330-Q1 in an OBC Application

8.2.1 Design Requirements

Table 1 lists the parameters for this typical application.

Table 1. Design Requirements

PARAMETER	VALUE
Low-side supply voltage	3.3 V or 5 V
Voltage drop across the sensing resistor for a linear response	1 V (maximum)
Current through the resistive divider, I_{CROSS}	100 μ A (maximum)

8.2.2 Detailed Design Procedure

8.2.2.1 Detailed Design Procedure

Use Ohm's Law to calculate the minimum total resistance of the resistive divider to limit the cross current to the desired value ($R_{TOTAL} = V_{LX} / I_{CROSS}$) and the required sense resistor value to be connected to the AMC3330-Q1 input: $R_{SNS} = V_{FSR} / I_{CROSS}$.

Consider the following two restrictions to choose the proper value of the sense resistor R_{SNS} :

- The voltage drop on R_{SNS} caused by the nominal voltage range of the system must not exceed the recommended input voltage range: $V_{SNS} \leq V_{FSR}$
- The voltage drop on R_{SNS} caused by the maximum allowed system overvoltage must not exceed the input voltage that causes a clipping output: $V_{SNS} \leq V_{Clipping}$

Table 2 lists examples of nominal E96-series (1% accuracy) resistor values for systems using 120-V and 230-V AC line voltages.

Table 2. Resistor Value Examples

PARAMETER	120-V _{RMS} LINE VOLTAGE	230-V _{RMS} LINE VOLTAGE
Peak voltage	170 V	325 V
Resistive divider resistors R_{L11} , R_{L12}	845 M Ω	1.62 M Ω
Sense resistor R_{SNS}	10 k Ω	10 k Ω
Current through resistive divider I_{CROSS}	100 μ A	100 μ A
Resulting voltage drop on sense resistor V_{SNS}	1.00 V	1.00 V

For systems using single-ended input ADCs to convert the analog output voltage into digital, Figure 9 shows an example of a TLV313-Q1-based signal conversion and filter circuit. With $R1 = R2 = R3 = R4$, the output voltage equals $(V_{OUTP} - V_{OUTN}) + 0.5 \times V_{REF}$. Tailor the bandwidth of this filter stage to the bandwidth requirement of the system and use NP0-type capacitors for best performance. For most applications, $R1 = R2 = R3 = R4 = 10$ k Ω and $C1 = C2 = 1000$ pF yields good performance.

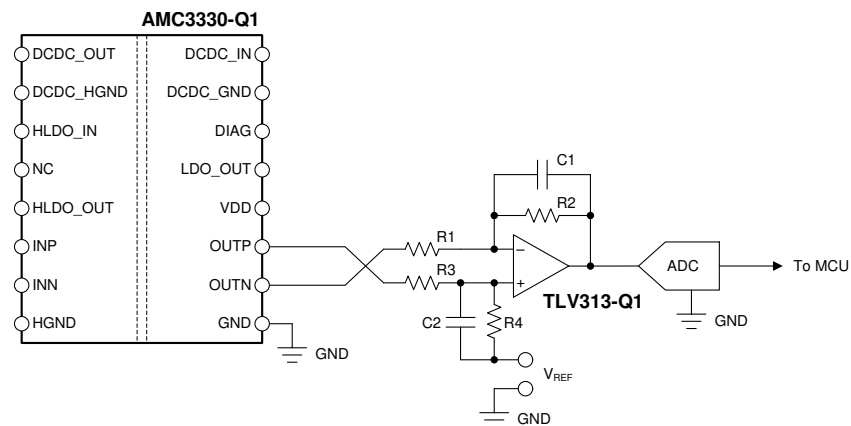


Figure 9. Connecting the Output to a Single-Ended Input ADC

For more information on the general procedure to design the filtering and driving stages of SAR ADCs, see the [18-Bit, 1MSPS Data Acquisition Block \(DAQ\) Optimized for Lowest Distortion and Noise](#) and [18-Bit Data Acquisition Block \(DAQ\) Optimized for Lowest Power](#) reference guides, available for download at www.ti.com.

The AMC3330-Q1 requires a single 3.3-V or 5-V supply on its low-side. The high-side supply is internally generated by an integrated DC/DC converter, as explained in the [Isolated DC/DC Converter](#) section.

8.2.2.2 Input Filter Design

TI recommends placing an RC filter in front of the isolated amplifier to improve signal-to-noise performance of the signal path. Design the input filter such that:

- The cutoff frequency of the filter is at least one order of magnitude lower than the sampling frequency (20 MHz) of the internal $\Delta\Sigma$ modulator
- The DC impedance of the filter does not generate significant voltage drop in the analog input lines
- The source impedance of the analog inputs are equal

For most applications the structure shown in [Figure 10](#) achieves excellent performance.

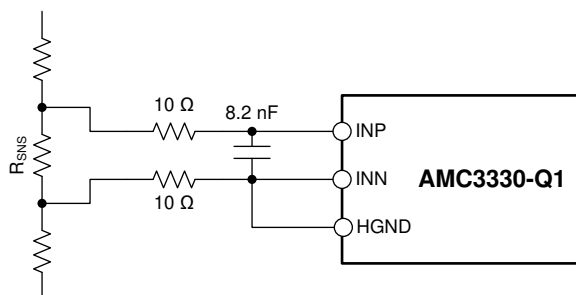


Figure 10. Differential Input Filter

8.3 What to Do and What Not to Do

Do not leave the analog inputs INP and INN of the AMC3330-Q1 unconnected (floating) when the device is powered up on the high-side. If the device input is left floating, the bias current may generate a negative input voltage that exceeds the specified input voltage range and the output of the device is invalid.

Connect the high-side ground (HGND) to INN, either directly or through a resistive path. A DC current path between INN and HGND is required to define the input common-mode voltage. Take care not to exceed the input common-mode range as specified in the *Electrical Characteristics* table in the [Specifications](#) section.

9 Power Supply Recommendations

The AMC3330-Q1 is powered from the low-side power supply (VDD) with a nominal value of 3.3 V (or 5 V) $\pm$ 10%. TI recommends a low-ESR decoupling capacitor of 1 nF (C8 in Figure 11) placed as close as possible to the VDD pin, followed by a 1- μ F capacitor (C9) to filter this power-supply path.

The primary-side of the DC/DC converter is decoupled with a low-ESR 100-nF capacitor (C4) positioned close to the device between the DCDC_IN and DCDC_GND pins. Use a 1- μ F capacitor (C2) to decouple the secondary side. Also in this case, use a low-ESR, 1-nF capacitor (C3) placed as close as possible to the device, connected to the DCDC_OUT and DCDC_HGND pins. The secondary-side ground reference DCDC_HGND is derived from the end of the sense resistor, which is connected to the negative input (INN) of the device.

For the secondary-side LDO, use low-ESR capacitors of 1-nF (C6), placed as close as possible to the AMC3330-Q1, followed by a 100-nF decoupling capacitor (C5).

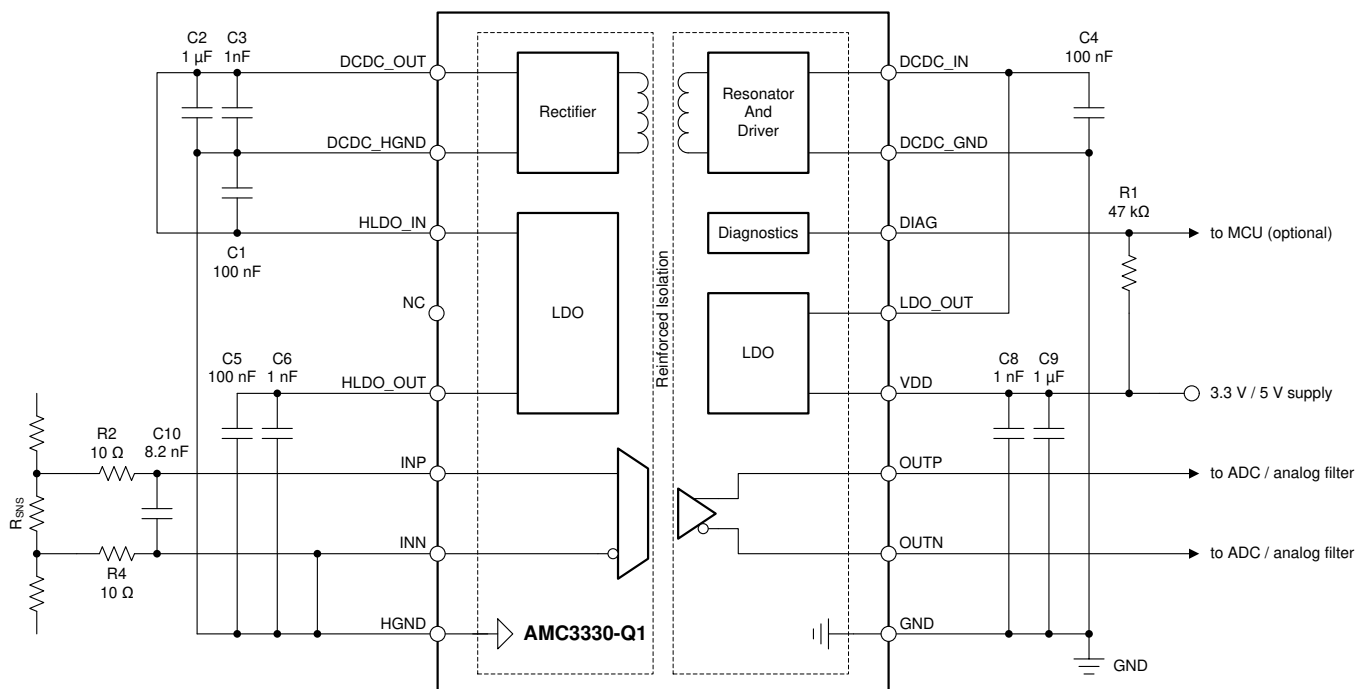


Figure 11. Decoupling the AMC3330-Q1

Capacitors must provide adequate *effective* capacitance under the applicable DC bias conditions they experience in the application. Multilayer ceramic capacitors (MLCC) capacitors typically exhibit only a fraction of their nominal capacitance under real-world conditions and this factor must be taken into consideration when selecting these capacitors. This problem is especially acute in low-profile capacitors, in which the dielectric field strength is higher than in taller components. Reputable capacitor manufacturers provide capacitance versus DC bias curves that greatly simplify component selection.

Table 3 lists components suitable for use with the AMC3330-Q1. This list is not exhaustive. Other components may exist that are equally suitable (or better), however these listed components have been validated during the development of the AMC3330-Q1.

Table 3. Recommended External Components

DESCRIPTION		PART NUMBER	MANUFACTURER	SIZE (EIA, L x W)
VDD				
C8	1 nF ± 10%, X7R, 50 V	12065C102KAT2A	AVX	1206, 3.2 mm x 1.6 mm
C9	1 μF ± 10%, X7R, 25 V	12063C105KAT2A	AVX	1206, 3.2 mm x 1.6 mm
DC/DC CONVERTER				
C4	100 nF ± 10%, X7R, 50 V	C0603C104K5RACAUTO	Kemet	0603, 1.6 mm x 0.8 mm
C3	1 nF ± 10%, X7R, 50 V	C0603C102K5RACTU	Kemet	0603, 1.6 mm x 0.8 mm
C2	1 μF ± 10%, X7R, 25 V	CGA3E1X7R1E105K080AC	TDK	0603, 1.6 mm x 0.8 mm
HLDO				
C1	100 nF ± 10%, X7R, 50 V	C0603C104K5RACAUTO	Kemet	0603, 1.6 mm x 0.8 mm
C5	100 nF ± 5%, NP0, 50 V	C3216NP01H104J160AA	TDK	1206, 3.2 mm x 1.6 mm
C6	1 nF ± 10%, X7R, 50 V	12065C102KAT2A	AVX	1206, 3.2 mm x 1.6 mm

10 Layout

10.1 Layout Guidelines

Figure 12 shows a layout recommendation with the critical placement of the decoupling capacitors. The same component reference designators are used as in the [Power Supply Recommendations](#) section. Decoupling capacitors are placed as close as possible to the AMC3330-Q1 supply pins. For best performance, place the sense resistor close to the INP and INN inputs of the AMC3330-Q1 and keep the layout of both connections symmetrical.

This layout is used on the AMC3330-Q1 EVM and supports CISPR-11 compliant electromagnetic radiation levels.

10.2 Layout Example

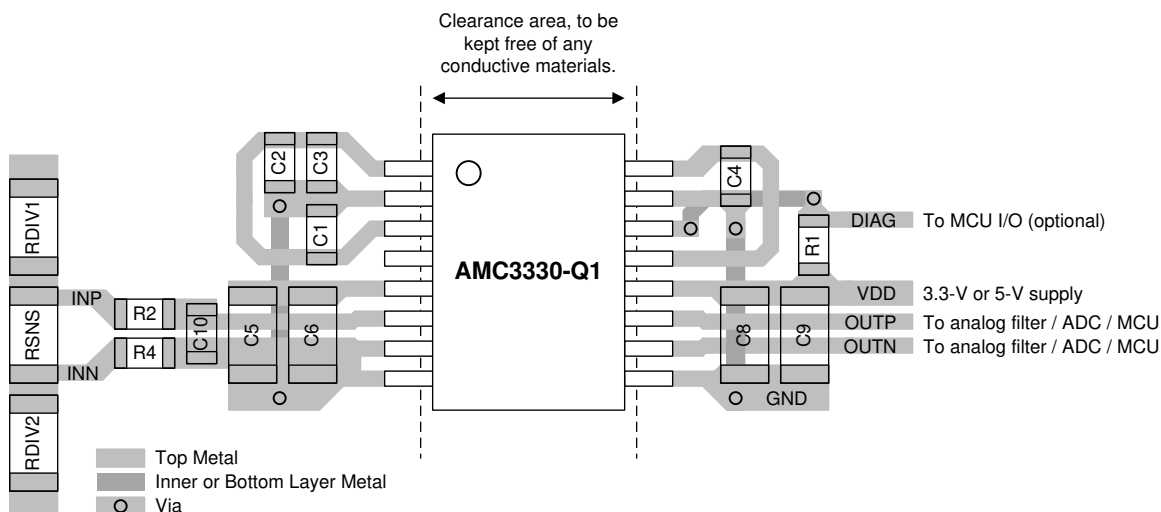


Figure 12. Recommended Layout of the AMC3330-Q1

11 Device and Documentation Support

11.1 Device Support

11.1.1 Device Nomenclature

Texas Instruments, [Isolation Glossary](#)

11.2 Documentation Support

11.2.1 Related Documentation

For related documentation see the following:

- Texas Instruments, [ISO72x Digital Isolator Magnetic-Field Immunity application report](#)
- Texas Instruments, [AMC3301 Precision, \$\pm 250\$ -mV Input, Reinforced Isolated Amplifier With Integrated DC/DC Converter data sheet](#)
- Texas Instruments, [TLVx313-Q1 Low-Power, Rail-to-Rail In/Out, 750- \$\mu\$ V Typical Offset, 1-MHz Operational Amplifier for Cost-Sensitive Systems data sheet](#)
- Texas Instruments, [18-Bit, 1MSPS Data Acquisition Block \(DAQ\) Optimized for Lowest Distortion and Noise reference guide](#)
- Texas Instruments, [18-Bit Data Acquisition Block \(DAQ\) Optimized for Lowest Power reference guide](#)

11.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.4 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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11.5 Trademarks

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11.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

11.7 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
AMC3330QDWERQ1	PREVIEW	SOIC	DWE	16	2000	TBD	Call TI	Call TI	-40 to 125		
PAMC3330QDWERQ1	ACTIVE	SOIC	DWE	16	2000	TBD	Call TI	Call TI	-40 to 125		Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

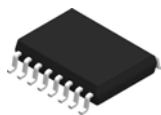
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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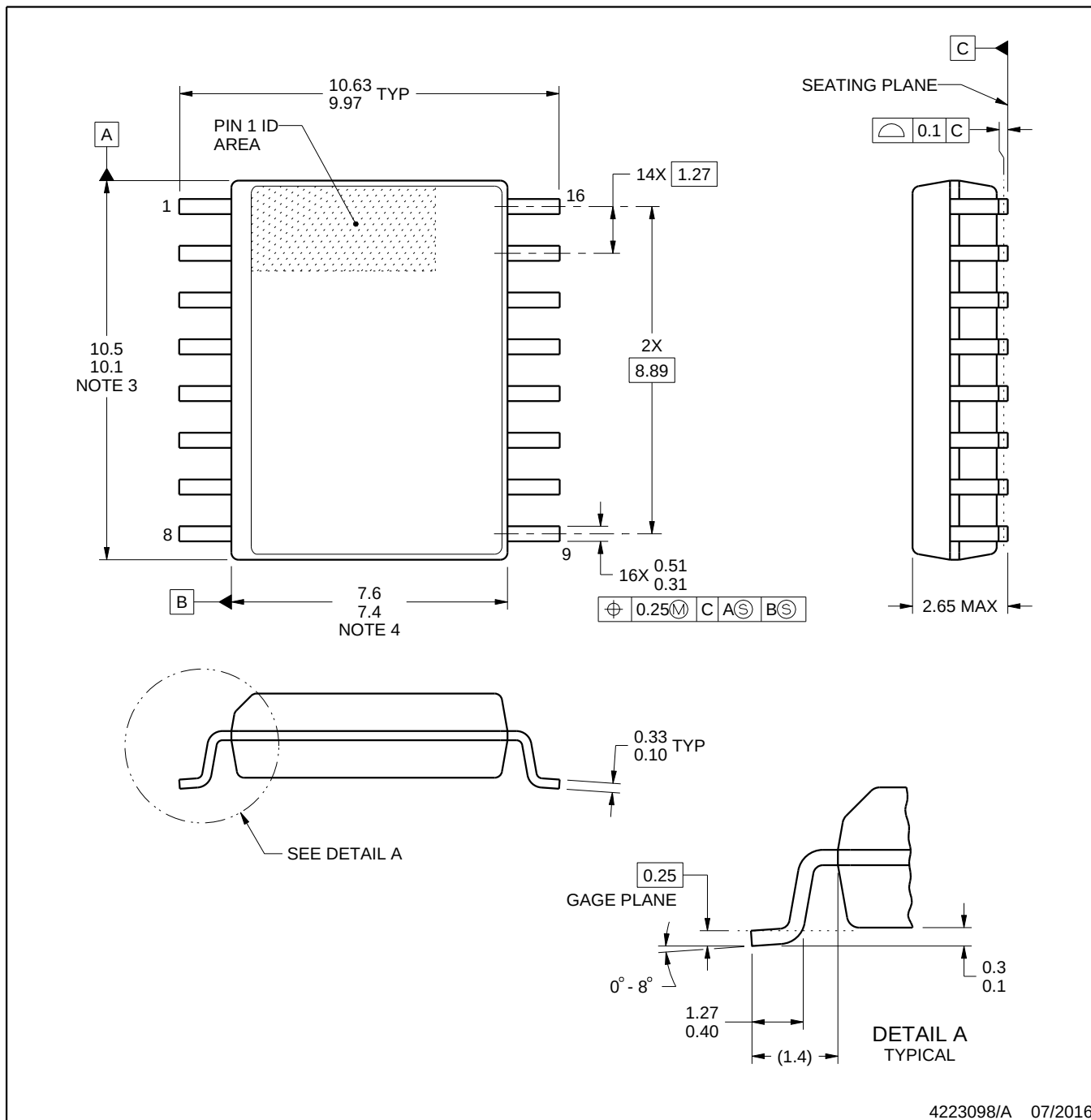
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



DWE0016A

PACKAGE OUTLINE **SOIC - 2.65 mm max height**

SOIC



4223098/A 07/2016

NOTES:

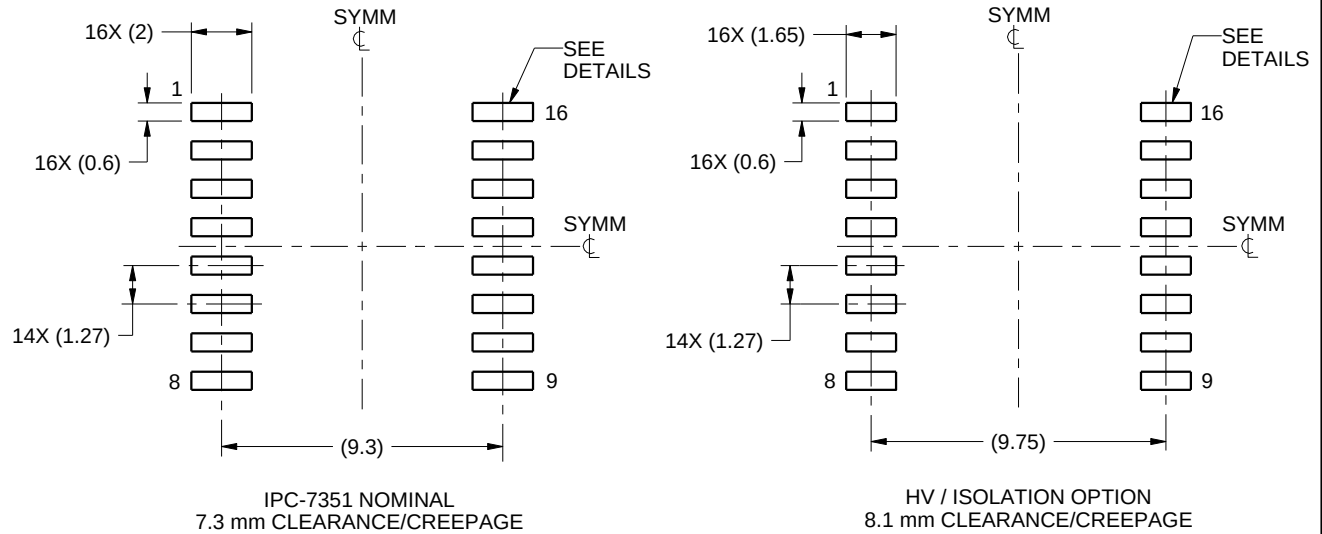
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
5. Reference JEDEC registration MS-013.

EXAMPLE BOARD LAYOUT

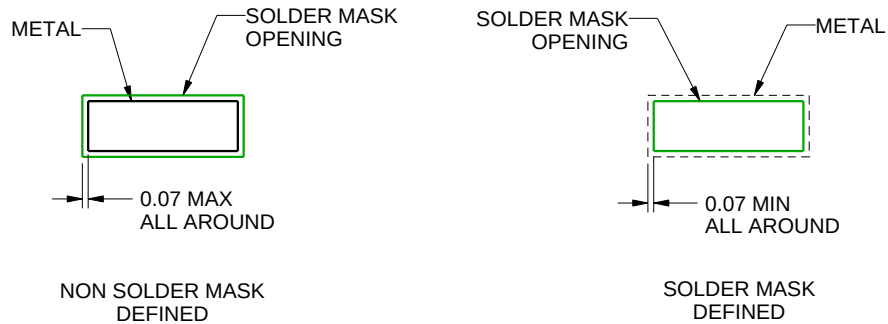
DWE0016A

SOIC - 2.65 mm max height

SOIC



LAND PATTERN EXAMPLE
SCALE:4X



SOLDER MASK DETAILS

4223098/A 07/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

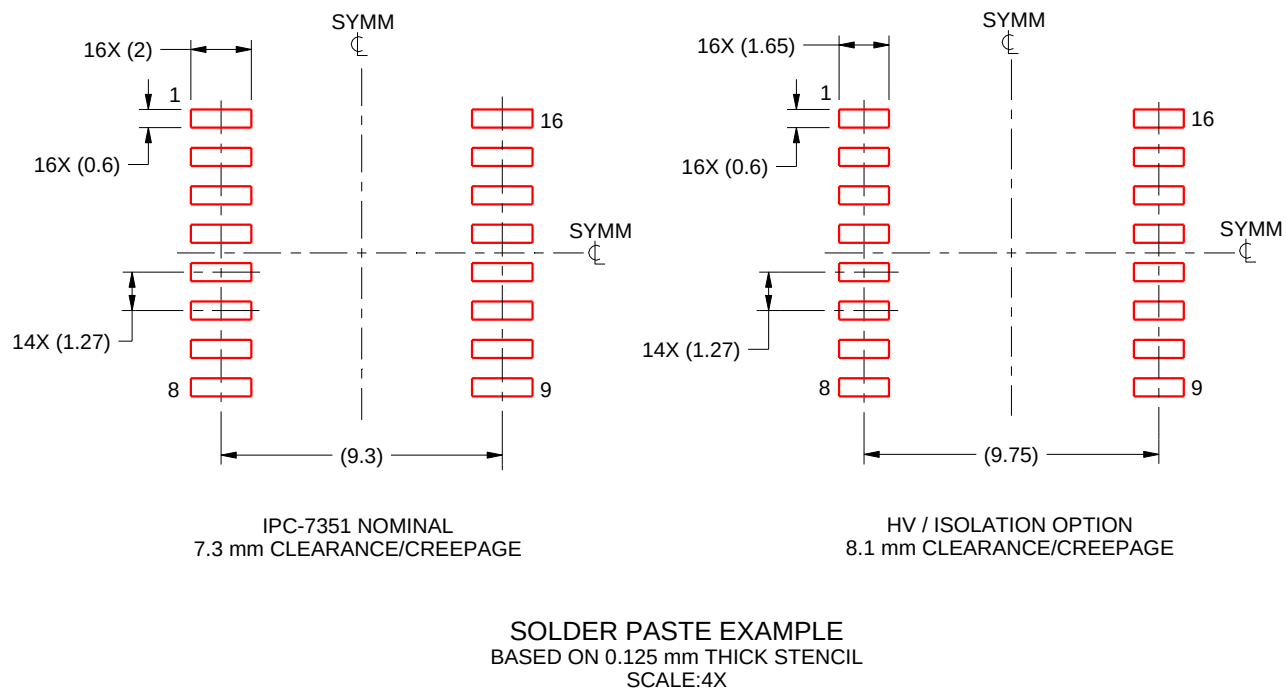
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DWE0016A

SOIC - 2.65 mm max height

SOIC



4223098/A 07/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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